

FS70KMJ-06F

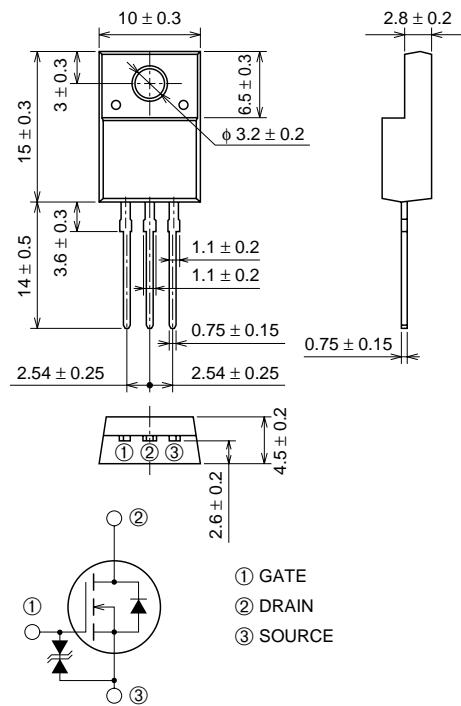
HIGH-SPEED SWITCHING USE

FS70KMJ-06F

- 4V DRIVE
- V_{DSS} 60V
- r_{D(S)} (ON) (MAX) 7.0mΩ
- I_D 70A
- Integrated Fast Recovery Diode (TYP.) 70ns

OUTLINE DRAWING

Dimensions in mm



TO-220FN

APPLICATION

Motor control, Lamp control, Solenoid control
DC-DC converter, etc.

MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$)

| Symbol | Parameter | Conditions | Ratings | Unit |
|------------------|----------------------------|-----------------------------------|------------|------|
| V _{DSS} | Drain-source voltage | V _{GS} = 0V | 60 | V |
| V _{GSS} | Gate-source voltage | V _{DS} = 0V | ±20 | V |
| I _D | Drain current | | 70 | A |
| I _{DM} | Drain current (Pulsed) | | 280 | A |
| I _{DA} | Avalanche current (Pulsed) | L = 10μH | 70 | A |
| I _S | Source current | | 70 | A |
| I _{SM} | Source current (Pulsed) | | 280 | A |
| P _D | Maximum power dissipation | | 30 | W |
| T _{ch} | Channel temperature | | -55 ~ +150 | °C |
| T _{stg} | Storage temperature | | -55 ~ +150 | °C |
| V _{iso} | Isolation voltage | AC for 1 minute, Terminal to case | 2000 | V |
| — | Weight | Typical value | 2.0 | g |

Mar. 2002

HIGH-SPEED SWITCHING USE**ELECTRICAL CHARACTERISTICS (T_{ch} = 25°C)**

| Symbol | Parameter | Test conditions | Limits | | | Unit |
|------------|----------------------------------|--|--------|------|------|------|
| | | | Min. | Typ. | Max. | |
| V (BR) DSS | Drain-source breakdown voltage | Id = 1mA, VGS = 0V | 60 | — | — | V |
| V (BR) GSS | Gate-source breakdown voltage | IG = ±100µA, VDS = 0V | ±20 | — | — | V |
| Idss | Drain-source leakage current | VDS = 60V, VGS = 0V | — | — | 100 | µA |
| IGSS | Gate-source leakage current | VGS = ±20V, VDS = 0V | — | — | ±10 | µA |
| VGS (th) | Gate-source threshold voltage | Id = 1mA, VDS = 10V | 1.0 | 1.5 | 2.0 | V |
| rDS (ON) | Drain-source on-state resistance | Id = 35A, VGS = 10V | — | 5.5 | 7.0 | mΩ |
| rDS (ON) | Drain-source on-state resistance | Id = 35A, VGS = 4V | — | 6.6 | 8.3 | mΩ |
| VDS (ON) | Drain-source on-state voltage | Id = 35A, VGS = 10V | — | 0.19 | 0.25 | V |
| yfs | Forward transfer admittance | Id = 35A, VDS = 10V | — | 110 | — | S |
| Ciss | Input capacitance | VDS = 10V, VGS = 0V, f = 1MHz | — | 8500 | — | pF |
| Coss | Output capacitance | | — | 1300 | — | pF |
| Crss | Reverse transfer capacitance | | — | 720 | — | pF |
| td (on) | Turn-on delay time | VDD = 30V, Id = 35A, VGS = 10V, RGEN = RGS = 50Ω | — | 42 | — | ns |
| tr | Rise time | | — | 130 | — | ns |
| td (off) | Turn-off delay time | | — | 800 | — | ns |
| tf | Fall time | | — | 330 | — | ns |
| VSD | Source-drain voltage | Is = 35A, VGS = 0V | — | 1.0 | 1.5 | V |
| Rth (ch-c) | Thermal resistance | Channel to case | — | — | 4.17 | °C/W |
| trr | Reverse recovery time | Is = 70A, dIs/dt = -100A/µs | — | 70 | — | ns |